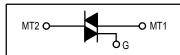
Triacs Silicon Bidirectional Thyristors

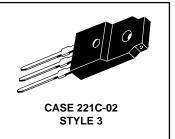
... designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity
 and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC210FP Series) or Four Modes (MAC210AFP Series)



ISOLATED TRIACs THYRISTORS 10 AMPERES RMS 200 thru 800 VOLTS

MAC210FP Series MAC210AFP Series



MAXIMUM RATINGS (T_J = 25° C unless otherwise noted.)

Rating	Symbol	Value	Unit	
Repetitive Peak Off-State Voltage ⁽¹⁾ (T _J = -40 to +125°C) 1/2 Sine Wave 50 to 60 Hz, Gate Open	VDRM		Volts	
MAC210-4FP, MAC210A4FP		200		
MAC210-6FP, MAC210A6FP		400		
MAC210-8FP, MAC210A8FP MAC210-10FP, MAC210A10FP		600 800		
On-State RMS Current (T _C = +70°C) Full Cycle Sine Wave 50 to 60 Hz ⁽²⁾	IT(RMS)	10	Amps	
Peak Nonrepetitive Surge Current (One Full Cycle, 60 Hz, T _C = +70°C) preceded and followed by rated current	ITSM	100	Amps	
Circuit Fusing (t = 8.3 ms)	l ² t	40	A ² s	
Peak Gate Power (T _C = +70°C, Pulse Width = 10 μ s)	PGM	20	Watts	
Average Gate Power ($T_C = +70^{\circ}C$, t = 8.3 ms)	PG(AV)	0.35	Watt	
Peak Gate Current (T _C = +70°C, Pulse Width = 10 μ s)	I _{GM}	2	Amps	
RMS Isolation Voltage (T _A = 25°C, Relative Humidity \leq 20%)	V _(ISO)	1500	Volts	
Operating Junction Temperature	TJ	-40 to +125	٥°	
Storage Temperature Range	T _{stg}	-40 to +125	٥°	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	2.2	°C/W
Thermal Resistance, Case to Sink	R ₀ CS	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	60	°C/W

1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

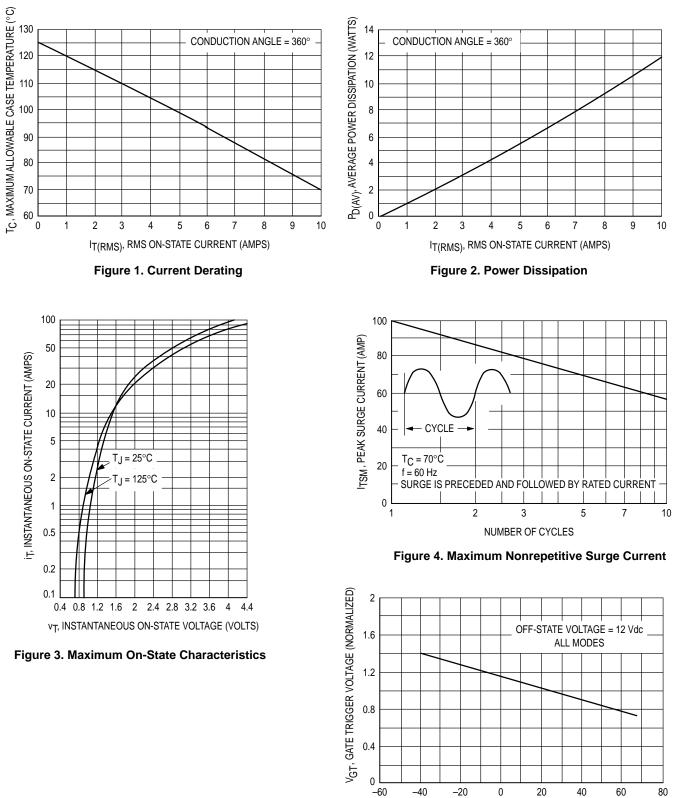
 $2. The case temperature reference point for all {\sf T}_C measurements is a point on the center lead of the package as close as possible to the plastic body.$



MAC210FP Series MAC210AFP Series

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current (Either Direction) (V _D = Rated V _{DRM} , Gate Open) $T_J = 25^{\circ}C$ $T_J = +125^{\circ}C$	IDRM		_	10 2	μA mA
Peak On-State Voltage (Either Direction) (I_{TM} = 14 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle $\leq 2\%$)	V _{TM}	-	1.2	1.65	Volts
Gate Trigger Current (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100$ Ohms Minimum Gate Pulse Width = 2 µs) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY	lGT	 	12 12 20 35	50 50 50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100$ Ohms Minimum Gate Pulse Width = 2 µs) MT2(+), G(+) MT2(-), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY (Main Terminal Voltage = Rated V _{DRM} , $R_L = 10$ k Ω , $T_J = +125^{\circ}$ C MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY	VGT	 0.2 0.2	0.9 0.9 1.1 1.4 	2 2 2.5 —	Volts
Holding Current (Either Direction) (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = 500 mA, $T_C = +25^{\circ}C$)	Ч	-	6	50	mA
Turn-On Time (Rated V _{DRM} , I _{TM} = 14 A, I _{GT} = 120 mA, Rise Time = 0.1 μ s, Pulse Width = 2 μ s)	^t gt	-	1.5	—	μs
Critical Rate of Rise of Commutation Voltage (V _D = Rated V _{DRM} , I _{TM} = 14 A, Commutating di/dt = 5.0 A/ms, Gate Unenergized, T _C = +70°C)	dv/dt _(c)	-	5	—	V/µs
Critical Rate of Rise of Off-State Voltage (V_D = Rated V_{DRM} , Exponential Voltage Rise, Gate Open, T_C = +70°C)	dv/dt	_	100	_	V/µs

MAC210FP Series MAC210AFP Series



TYPICAL CHARACTERISTICS

Figure 5. Typical Gate Trigger Voltage

T_C, CASE TEMPERATURE (°C)

MAC210FP Series MAC210AFP Series

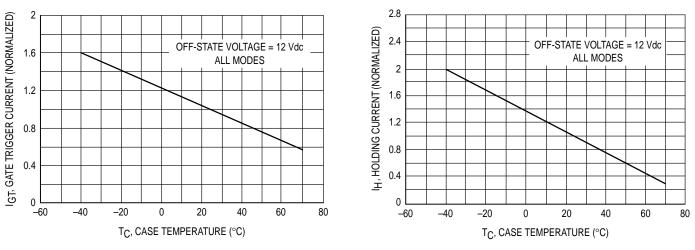


Figure 6. Typical Gate Trigger Current

Figure 7. Typical Holding Current

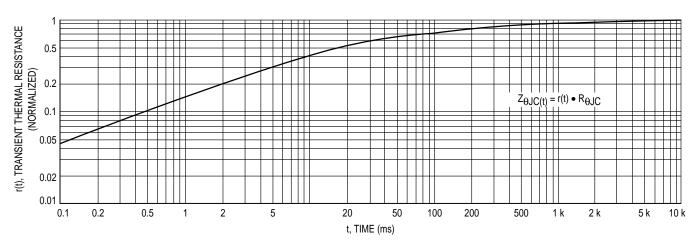
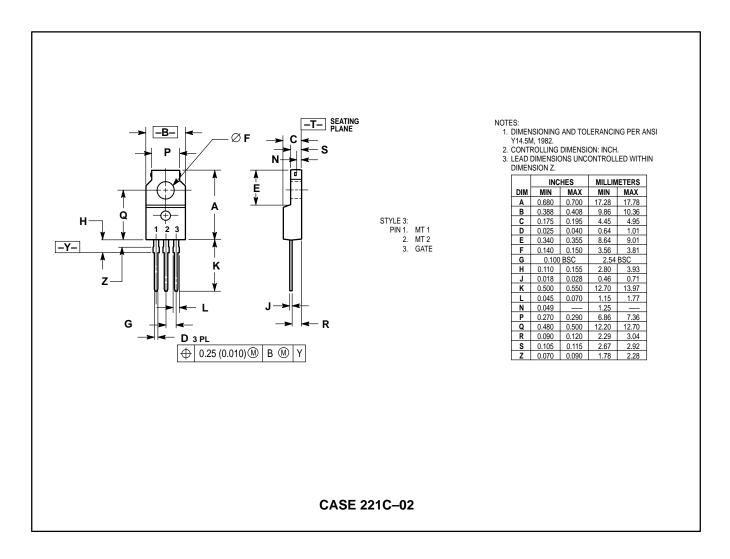


Figure 8. Thermal Response

PACKAGE DIMENSIONS



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